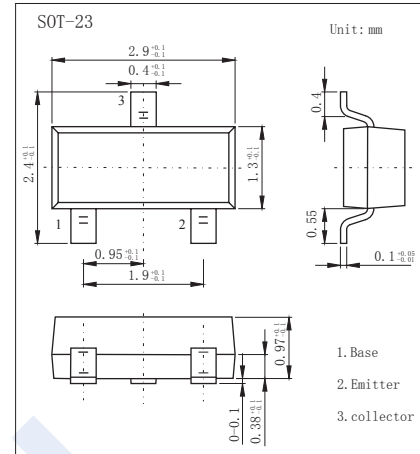


NPN Transistors

2SC3134

■ Features

- High V_{EBO} .
- Wide ASO and high durability against breakdown.
- Complementary to 2SA1252

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	60	V
Collector - Emitter Voltage	V_{CEO}	50	
Emitter - Base Voltage	V_{EBO}	15	
Collector Current - Continuous	I_C	150	mA
Collector Current - Pulse	I_{CP}	300	
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu\text{A}$, $I_E = 0$	60			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 \text{ mA}$, $I_B = 0$	50			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu\text{A}$, $I_C = 0$	15			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 40 \text{ V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 10 \text{ V}$, $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50 \text{ mA}$, $I_B = 5 \text{ mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50 \text{ mA}$, $I_B = 5 \text{ mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 6 \text{ V}$, $I_C = 1 \text{ mA}$	90		600	
Collector output capacitance	C_{ob}	$V_{CB} = 6 \text{ V}$, $f = 1 \text{ MHz}$		2.2		pF
Transition frequency	f_T	$V_{CE} = 6 \text{ V}$, $I_C = 1 \text{ mA}$		100		MHz

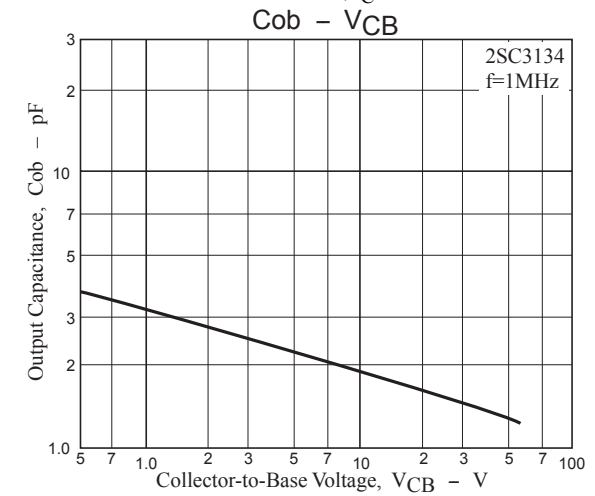
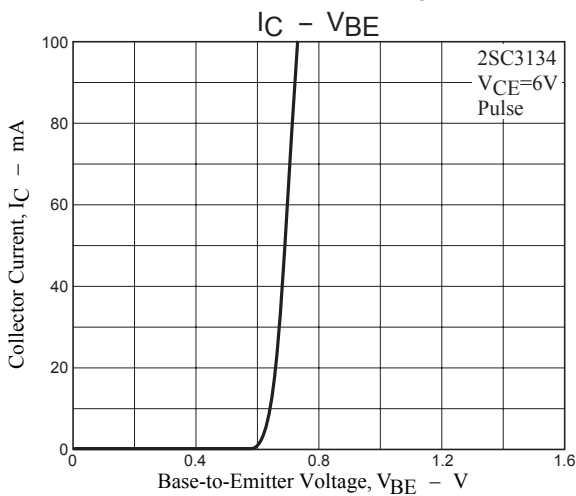
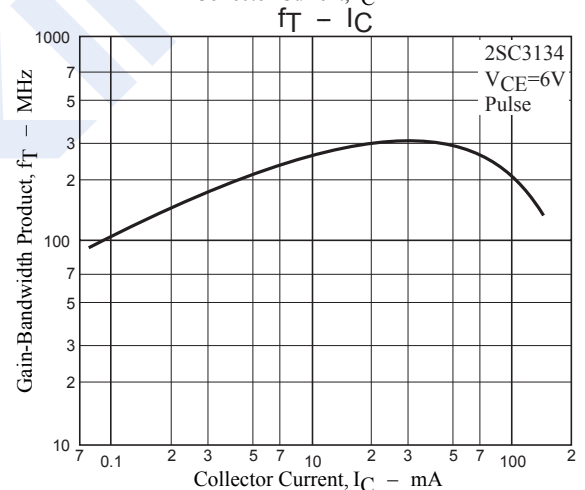
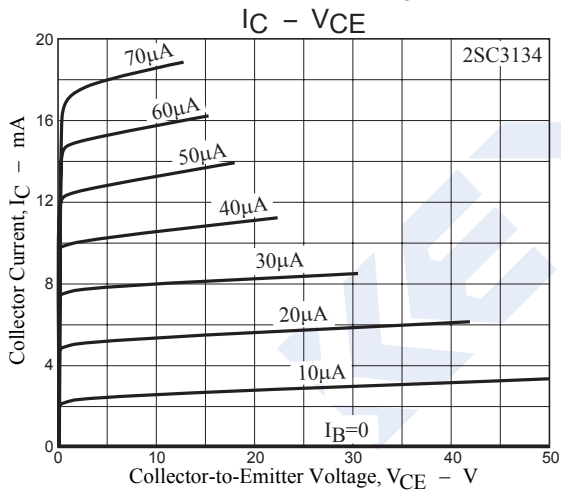
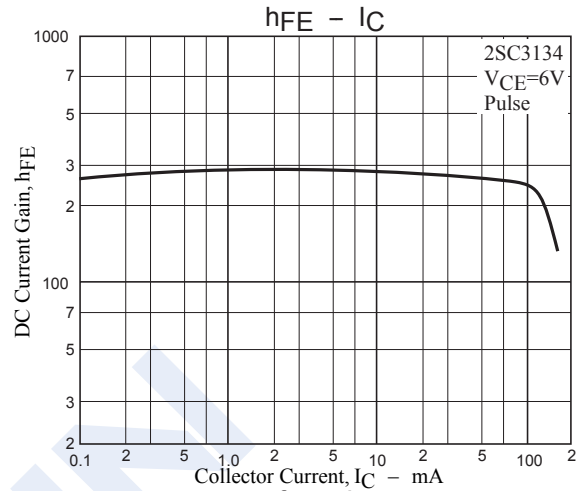
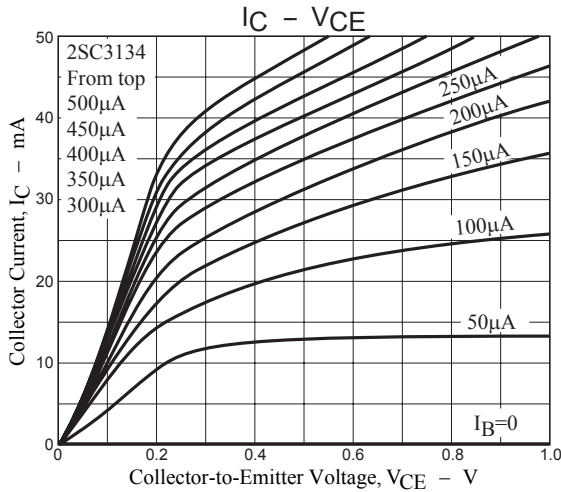
■ Classification of h_{fe}

Marking	H4	H5	H6	H7
Range	90-180	135-270	200-400	300-600

NPN Transistors

2SC3134

■ Typical Characteristics



NPN Transistors

2SC3134

■ Typical Characteristics

